



HAICHUANG SEMI

BC846/847/848/849/850

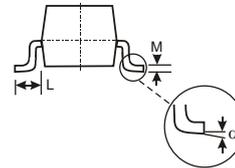
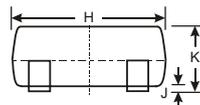
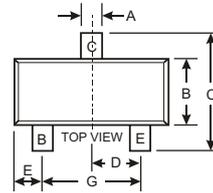
NPN SILICON AF TRANSISTOR

Features

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage

MARKING

TYPER	MARKING	TYPER	MARKING
BC846A	1A	BC848C	1L
BC846B	1B	BC849A	2A
BC846C	1C	BC849B	2B
BC847A	1E	BC849C	2C
BC847B	1F	BC850A	2E
BC847C	1G	BC850B	2F
BC848A	1J	BC850C	2G
BC848B	1K		



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Units	
Collector Base Voltage	BC846	V_{CBO}	80	V
	BC847, BC850	V_{CBO}	50	V
	BC848, BC849	V_{CBO}	30	V
Collector Emitter Voltage	BC846	V_{CEO}	65	V
	BC847, BC850	V_{CEO}	45	V
	BC848, BC849	V_{CEO}	30	V
Emitter Base Voltage	BC846, BC847	V_{EBO}	6	V
	BC848, BC849, BC850	V_{EBO}	5	V
Collector Current	I_C	100	mA	
Peak Collector Current	I_{CM}	200	mA	
Power Dissipation	P_{tot}	300	mW	
Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature Range	T_S	- 65 to + 150	$^\circ\text{C}$	



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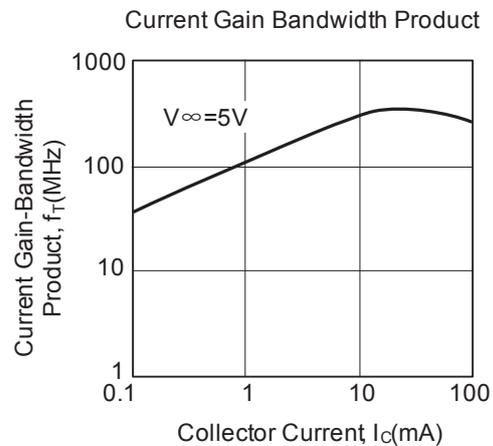
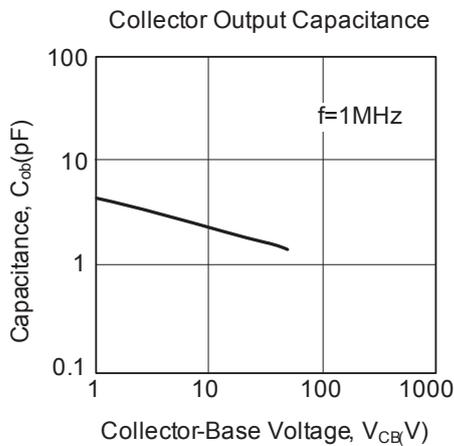
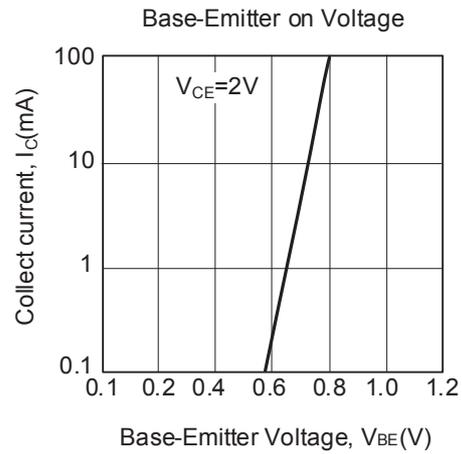
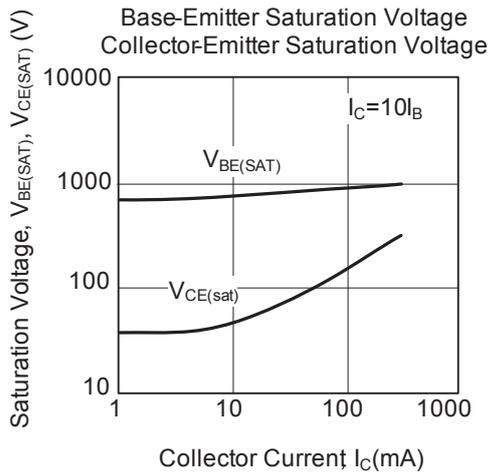
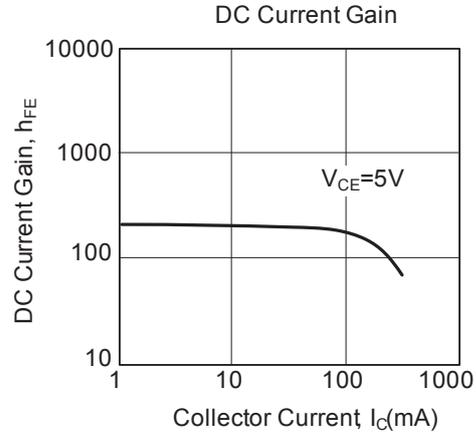
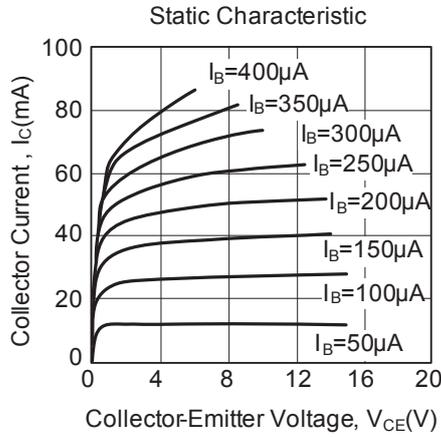
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Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Units
Collector-base breakdown voltage at $I_C = 10 \mu\text{A}$, $I_E = 0$	BC846 BC847/850 BC848/849 $V_{(BR)CBO}$	80 50 30			
Collector-emitter breakdown voltage at $I_C = 10 \text{mA}$, $I_B = 0$	BC846 BC847/850 BC848/849 $V_{(BR)CEO}$	65 45 30			
Emitter-base breakdown voltage at $I_E = 1 \mu\text{A}$, $I_C = 0$	BC846/847 BC848-850 $V_{(BR)EBO}$	6 5			
DC Current Gain at $V_{CE} = 5 \text{V}$, $I_C = 2 \text{mA}$	A B C h_{FE}	110 200 420	- - -	220 450 800	- - -
Collector Emitter Saturation Voltage at $I_C = 10 \text{mA}$, $I_B = 0.5 \text{mA}$ at $I_C = 100 \text{mA}$, $I_B = 5 \text{mA}$	V_{CEsat} V_{CEsat}	- -	- -	250 600	mV mV
Base-emitter saturation voltage at $I_C = 10 \text{mA}$, $I_B = 0.5 \text{mA}$ at $I_C = 100 \text{mA}$, $I_B = 5 \text{mA}$	V_{BEsat} V_{BEsat}	- -	700 900	850 1100	mV mV
Base Emitter On Voltage at $I_C = 2 \text{mA}$, $V_{CE} = 5 \text{V}$ at $I_C = 10 \text{mA}$, $V_{CE} = 5 \text{V}$	$V_{BE(on)}$ $V_{BE(on)}$	580 -	- -	700 770	mV mV
Collector Cutoff Current at $V_{CB} = 30 \text{V}$	I_{CBO}	-	-	15	nA
Current Gain Bandwidth Product at $V_{CE} = 5 \text{V}$, $I_C = 10 \text{mA}$, $f = 100 \text{MHz}$	f_T	-	300	-	MHz
Output Capacitance at $V_{CB} = 10 \text{V}$, $f = 1 \text{MHz}$	C_{ob}	-	-	6	pF
Input Capacitance at $V_{EB} = 0.5 \text{V}$, $f = 1 \text{MHz}$	C_{ib}	-	9	-	pF
Noise Figure at $I_C = 200 \mu\text{A}$, $V_{CE} = 5 \text{V}$ $R_G = 2 \text{K}\Omega$, $f = 1 \text{KHz}$ at $I_C = 200 \mu\text{A}$, $V_{CE} = 5 \text{V}$, $R_G = 2 \text{K}\Omega$, $f = 30 \sim 15 \text{KHz}$	BC846, BC847, BC848 BC849, BC850 BC849 BC850 NF	- - - -	- - - -	10 4 4 3	dB dB dB dB

TYPICAL TRANSIENT CHARACTERISTICS



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